

LED780-66-60

TECHNICAL DATA

High Power LED Array, 60 chips

LED780-66-60 is a wide viewing and extremely high output power illuminator assembled with a total of 60 high efficiency AlGaAs diode chips, mounted on a metal stem TO-66 with AIN ceramics and covered with double coated clear silicone and epoxy resin.

These devices are designed for high current operation with proper heat sinking to improver thermal conductive efficiency.

Specifications

- Structure: AlGaAs, 60 LED chips
- Peak Wavelength: typ. 780 nm
- Optical Output Power: typ. 1 W
- Package: TO-66 stem with AIN, clear silicon and epoxy resin

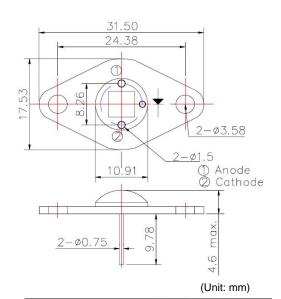
Absolute Maximum Ratings (T_c=25°C)

Item	Symbol	Value	Unit
Power Dissipation	PD	7.8	W
Forward Current	I _F	750	mA
Pulsed Forward Current *1	I _{FP}	3	А
Reverse Voltage	V _R	50	V
Operating Temperature	T _{opr}	-30 +80	°C
Storage Temperature	T _{stg}	-30 +110	°C
Soldering Temperature *2	T _{sol}	240	°C

 *1 duty = 1%, pulse width = 1 µs

*² must be completed within 3 seconds

Electro-Optical Characteristics





Item	Symbol	Condition	Min.	Тур.	Max.	Unit
Total Radiated Power	Po	I _F = 600 mA	-	1	-	W
Total Radiated Power	Po	$I_F = 3 A$	-	4	-	W
Radiant Intensity	Ι _Ε	$I_{\rm F} = 600 {\rm mA}$	-	450	-	mW/sr
Forward Voltage	V _F	$I_{\rm F} = 600 {\rm mA}$	-	9.0	-	V
Reverse Voltage	V _R	I _R = 10 μA	50	-	-	V
Peak Wavelength	λ _P	$I_{\rm F} = 600 {\rm mA}$	-	780	-	nm
Half Width	Δλ	$I_{\rm F} = 600 {\rm mA}$	-	30	-	nm
Viewing Half Angle	Θ _{1/2}	$I_{\rm F} = 600 {\rm mA}$	-	±60	-	deg.
Rise Time	t _r	$I_{\rm F} = 600 {\rm mA}$	-	100	-	ns
Fall Time	t _f	I _F = 600 mA	-	100	-	ns

Heat Sink is required, thermal resistance <8K/W

Notes

- This high power LED must be cooled!
- Do not view directly into the emitting area of the LED during operation!
- The above specifications are for reference purpose only and subjected to change without prior notice.







Typical Performance Curves

